

second position with the reflected energy corresponding to the high energy is started.

58. (Amended) [A] The method of forming a crystalline film according to Claim [Claims 56 and] 57, wherein the first position is substantially the same as the second position.

59. (Amended) [A] The method of forming a crystalline film according to Claim 56 [Claims 56 to 58], wherein the thin film is a semiconductor thin film.

60. (Amended) [A] The method of forming a crystalline film according to Claim 56 [Claims 56 to 58], wherein the thin film is a metallic thin film.

61. (Amended) [A] The method of forming a crystalline film according to Claim 56 [Claims 56 to 60], wherein the form of the high energy is light.

62. (Amended) [A] The method of manufacturing a thin film electronic device comprising a crystalline film, wherein the crystalline film is formed by a method according to Claim 1 [any one of Claims 1 to 18, 20 to 23, 25 to 28, 30 to 33, 35 to 38, 40 to 43, 46 to 49, and 56 to 61].

REMARKS

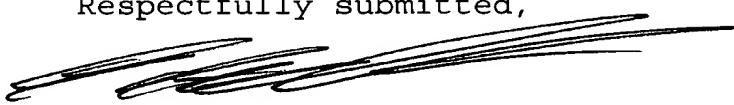
Claims 1-62 are pending. By this Preliminary Amendment, claims 1-62, the Specification and Abstract are amended.

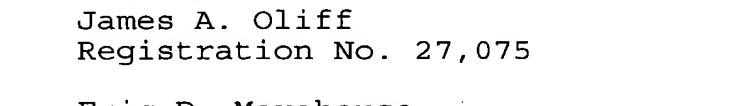
A substitute Specification and substitute Abstract are provided. For the Examiner's convenience, a working copy of original Specification and Abstract is attached. No new matter is added to the Specification or Abstract.

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Prompt and favorable examination on the merits is respectfully requested.

Respectfully submitted,

  
James A. Oliff  
Registration No. 27,075

  
Eric D. Morehouse  
Registration No. 38,565

JAO:EDM/kmg

OLIFF & BERRIDGE  
P.O. Box 19928  
Alexandria, Virginia 22320  
Telephone: (703) 836-6400